

PF01411B

MOS FET Power Amplifier Module for E-GSM Handy Phone

HITACHI

ADE-208-434B (Z)
3rd Edition
Nov. 1997

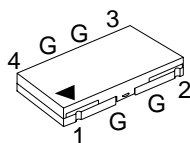
Application

- For E-GSM class4 880 to 915 MHz
- For 3.5 V nominal battery use

Features

- High gain 3stage amplifier : 0 dBm input
- Lead less thin & Small package : 2 mm Max, 0.2cc
- High efficiency : 45% Typ at 35.5 dBm
- Wide gain control range : 70 dB Typ

Pin Arrangement



1: Pin
2: V_{apc}
3: V_{dd}
4: P_{out}
G: GND

Absolute Maximum Ratings (T_c = 25°C)

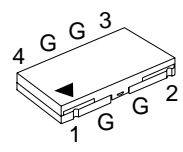
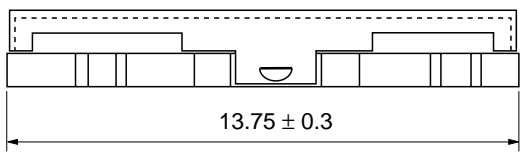
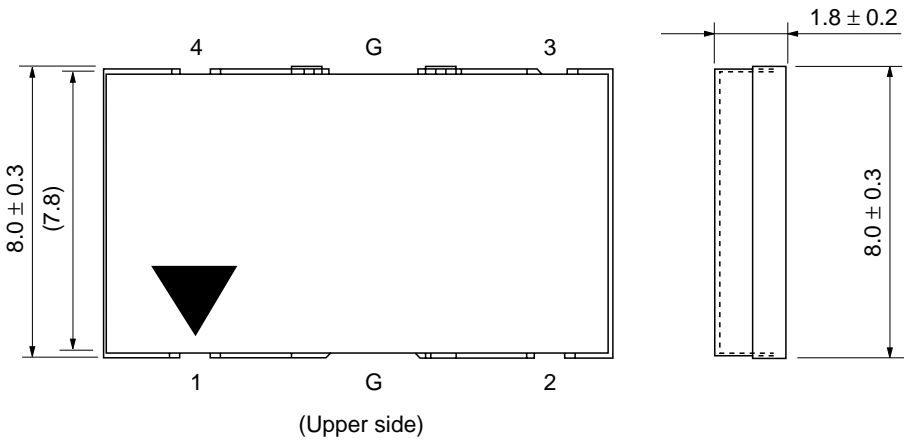
Item	Symbol	Rating	Unit
Supply voltage	V _{DD}	8	V
Supply current	I _{DD}	3	A
V _{APC} voltage	V _{APC}	4	V
Input power	P _{in}	10	mW
Operating case temperature	T _c (op)	-30 to +100	°C
Storage temperature	T _{stg}	-30 to +100	°C
Output power	P _{out}	5	W

Electrical Characteristics (T_c = 25°C)

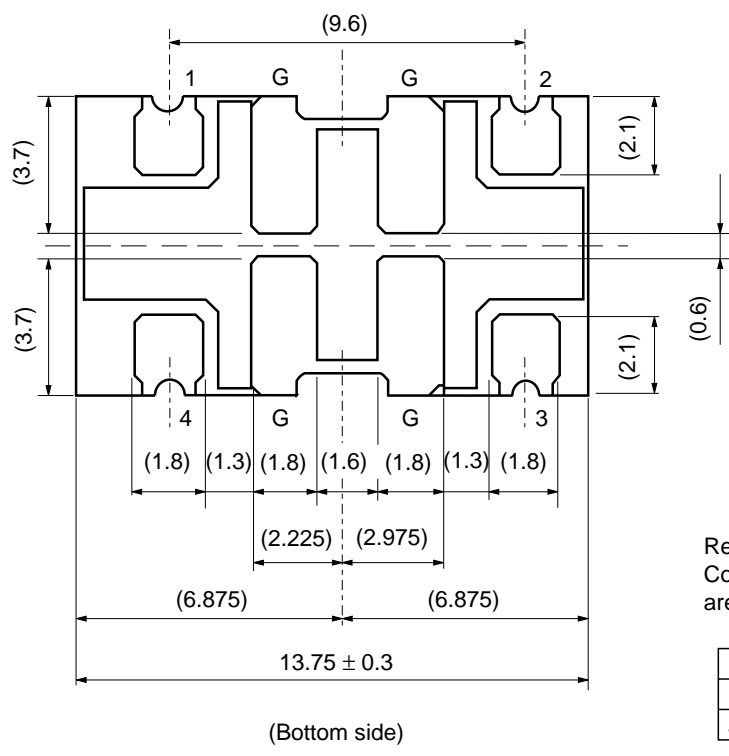
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Frequency range	f	880	—	915	MHz	
Control voltage range	V _{APC}	0.5	—	2.2	V	
Drain cutoff current	I _{DS}	—	—	100	μA	V _{DD} = 8V, V _{APC} = 0V
Total efficiency	η _T	40	45	—	%	Pin = 0dBm, V _{DD} = 3.5V,
2nd harmonic distortion	2nd H.D.	—	-45	-35	dBc	Pout = 35.5dBm, Vapc = control
3rd harmonic distortion	3rd H.D.	—	-45	-35	dBc	R _L = R _g = 50Ω, T _c = 25°C
Input VSWR	VSWR (in)	—	1.5	3	—	
Output power (1)	Pout (1)	35.5	36.0	—	dBm	Pin = 0dBm, V _{DD} = 3.5V, V _{APC} = 2.2V, R _L = R _g = 50Ω, T _c = 25°C
Output power (2)	Pout (2)	33.5	34.2	—	dBm	Pin = 0dBm, V _{DD} = 3.0V, V _{APC} = 2.2V, R _L = R _g = 50Ω, T _c = 85°C
Isolation	—	—	-40	-36	dBm	Pin = 0dBm, V _{DD} = 3.5V, V _{APC} = 0.5V, R _L = R _g = 50Ω, T _c = 25°C
Switching time	tr, tf	—	1	2	μs	Pin = 0dBm, V _{DD} = 3.5V, Pout = 0 to 35.5dBm R _L = R _g = 50Ω, T _c = 25°C
Stability	—	No parasitic oscillation			—	Pin = 0dBm, V _{DD} = 3 to 5.1V, Pout ≤ 35.5dBm, Vapc ≤ 2.2V GSM pulse. R _g = 50Ω, T _c = 25°C, Output VSWR = 6 : 1 All phases
Load VSWR tolerance	—	No degradation			—	Pin = 0dBm, V _{DD} = 3 to 5.1V, Pout ≤ 35.5dBm, Vapc ≤ 2.2V GSM pulse. R _g = 50Ω, t = 20sec., T _c = 25°C, Output VSWR = 10 : 1 All phases

Package Dimensions

Unit: mm



- Pin arrangement
 1: Pin
 2: Vapc
 3: Vdd
 4: Pout
 G: GND



Remark:
 Coplanarity of bottom side of terminals are less than 0 +/- 0.1mm.

Hitachi code	RF-K
EIAJ code	
JEDEC code	

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